Table Captions

Chapter 2

Table 2.1 Sample identification and implantation conditions for the NiSi(615Å)/Si samples.

Table 2.2 Nickel silicide phase in the sample of NiSi/Si with/without BF_2^+, P^+ and P^+/F^+ implantation followed by annealing treatment at various temperatures.

Chapter 3

Table 3.1 Junction depths (in unit of nm) of NiSi(310Å)/p^+n junctions formed by ITS scheme with BF_2^+ implantation at various energies to a dose of $5\times10^{15}cm^{-2}$ followed by a 30 min thermal annealing.

Table 3.2 Junction depths (in unit of nm) of NiSi(310Å)/p^+n junctions formed by ITS scheme with BF_2^+ implantation to a dose of $5\times10^{15}cm^{-2}$ followed by a 30 sec RTA.

Chapter 4

Table 4.1 Junction depths (in unit of nanometer) of NiSi(615Å)/n^+p junction diodes studied in this work.